WHAT IS CLAIMED IS:

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1. An apparatus for providing an input output from an integrated circuit, the apparatus comprising:

an input/output (I/O) pad;

an upper pair of P-channel Metal Oxide Semiconductor (PMOS) devices, a first of the upper PMOS devices having source coupled to a power supply (V_{DDO}) and drain coupled to source of a second upper PMOS device, the second PMOS device having drain coupled to the I/O pad;

a lower pair of N-channel MOS devices (NMOS), a first of the upper NMOS devices having a drain coupled to the I/O pad and a source coupled to a drain of a second lower NMOS device, the second NMOS device having a source coupled to a ground potential;

a first bias circuit coupled to a gate of the first upper PMOS device, said bias circuit providing a first bias voltage to the gate of the first upper PMOS device when the I/O pad is in an output mode and V_{DDO} voltage otherwise;

a second bias circuit coupled to a gate of the second lower NMOS device, said bias circuit providing a second bias voltage to the gate of the second lower NMOS device when the I/O pad is in an output mode and a ground voltage otherwise;

a third bias circuit coupled to a gate of the second upper PMOS device, said bias circuit providing a third bias voltage, coupled to the gate of the second upper MOS device; and

a fourth bias circuit coupled to a gate of the first lower NMOS device, said bias circuit providing a fourth bias voltage to the gate of the first lower MOS device, the fourth bias voltage being in a range, the range having a maximum value of $V_{DDP} + V_T$ and a minimum value of $(V_{DDO} - V_{Tp})$, where V_{DDP} and V_{DDO} are power supply voltages and V_T and V_{Tp} are offset voltages.

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- 2. The apparatus of claim 1 wherein V_{DDO} and V_{DDP} are the same power supply.
- 3. The apparatus of claim 1 wherein V_{T} and V_{Tp} are the same offset voltages.
- 4. An apparatus for providing an input output from an integrated circuit, the apparatus comprising:

an input/output (I/O) pad;

an upper pair of P-channel Metal Oxide Semiconductor (PMOS) devices, a first of the upper PMOS devices having source coupled to a power supply (V_{DDO}) and drain coupled to source of a second upper PMOS device, the second PMOS device having drain coupled to the I/O pad;

a lower pair of N-channel MOS devices (NMOS), a first of the upper NMOS devices having a drain coupled to the I/O pad and a source coupled to a drain of a second lower NMOS device, the second NMOS device having a source coupled to a ground potential;

a first bias circuit coupled to a gate of the first upper PMOS device, said bias circuit providing a first bias voltage to the gate of the first upper PMOS device when the I/O pad is in an output mode and V_{DDO} voltage otherwise;

a second bias circuit coupled to a gate of the second lower NMOS device, said bias circuit providing a second bias voltage to the gate of the second lower NMOS device when the I/O pad is in an output mode and a ground voltage otherwise;

a third bias circuit coupled to a gate of the second upper PMOS device, said bias circuit providing a third bias voltage to the gate of the second upper MOS device; and

a fourth bias circuit coupled to a gate of the first lower NMOS device, said bias circuit providing a fourth bias voltage to the gate of the first lower MOS device depending on

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the voltage on the I/O pad (V_{PAD}) when the pad is in an output disable mode, and said bias circuit providing a fixed fourth bias voltage to the gate of the first lower MOS device when the pad is in an output enable mode.

- 5. The apparatus of claim 4 wherein the fixed fourth bias voltage is $V_{\text{DDP}}\,.$
- 6. An apparatus for providing an input output from an integrated circuit, the apparatus comprising:

an input/output (I/O) pad;

- an upper pair of P-channel Metal Oxide Semiconductor (PMOS) devices, a first of the upper PMOS devices having source coupled to a power supply (V_{DDO}) and drain coupled to source of a second upper PMOS device, the second PMOS device having drain coupled to the I/O pad;
- a lower pair of N-channel MOS devices (NMOS), a first of the upper NMOS devices having a drain coupled to the I/O pad and a source coupled to a drain of a second lower NMOS device, the second NMOS device having a source coupled to a ground potential;
- a first bias circuit coupled to a gate of the first upper PMOS device, said bias circuit providing a first bias voltage to the gate of the first upper PMOS device when the I/O pad is in an output mode and V_{DDO} voltage otherwise;
- a second bias circuit coupled to a gate of the second lower NMOS device, said bias circuit providing a second bias voltage to the gate of the second lower NMOS device when the I/O pad is in an output mode and a ground voltage otherwise;
- a third bias circuit coupled to a gate of the second upper PMOS device, said bias circuit providing a third bias voltage to the gate of the second upper MOS device equal to the voltage on the I/O pad (V_{PAD}) when the pad is in an output

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disable mode, and where the third bias voltage to the gate of the second upper MOS device equal to a fixed voltage when the pad is in an output enabled mode; and

a fourth bias circuit coupled to a gate of the first lower NMOS device, said bias circuit providing a fourth bias voltage to the gate of the first lower MOS device.

- 10 7. The apparatus of claim 6 wherein the fixed voltage is V_{DDC} .
 - 8. An apparatus for providing an input output from an integrated circuit, the apparatus comprising:

an input/output (I/O) pad;

an upper pair of P-channel Metal Oxide Semiconductor (PMOS) devices, a first of the upper PMOS devices having source coupled to a power supply (V_{DDO}) and drain coupled to source of a second upper PMOS device, the second PMOS device having drain coupled to the I/O pad;

a lower pair of N-channel MOS devices (NMOS), a first of the upper NMOS devices having a drain coupled to the I/O pad and a source coupled to a drain of a second lower NMOS device, the second NMOS device having a source coupled to a ground potential;

a first bias circuit coupled to a gate of the first upper PMOS device, said bias circuit providing a first bias voltage to the gate of the first upper PMOS device when the I/O pad is in an output mode and V_{DDO} voltage otherwise;

a second bias circuit coupled to a gate of the second lower NMOS device, said bias circuit providing a second bias voltage to the gate of the second lower NMOS device when the I/O pad is in an output mode and a ground voltage otherwise;

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- a third bias circuit coupled to a gate of the second upper PMOS device, said bias circuit providing a third bias voltage to the gate of the second upper MOS device; and
- a fourth bias circuit coupled to a gate of the first lower NMOS device, said bias circuit providing a fourth bias voltage to the gate of the first lower MOS device depending on the voltage on the I/O pad (V_{PAD}) , said fourth bias circuit comprising a capacitive voltage divider.
- 9. The apparatus of claim 8 wherein the capacitive voltage divider proportions the difference between a pad and power supply voltage to derive the fourth bias voltage, when a voltage provided to the pad is changing.
- 10. An apparatus for providing an input output from an integrated circuit, the apparatus comprising:

an input/output (I/O) pad;

- an upper pair of P-channel Metal Oxide Semiconductor (PMOS) devices, a first of the upper PMOS devices having source coupled to a power supply (V_{DDO}) and drain coupled to source of a second upper PMOS device, the second PMOS device having drain coupled to the I/O pad;
- a lower pair of N-channel MOS devices (NMOS), a first of the upper NMOS devices having a drain coupled to the I/O pad and a source coupled to a drain of a second lower NMOS device, the second NMOS device having a source coupled to a ground potential;
- a first bias circuit coupled to a gate of the first upper PMOS device, said bias circuit providing a first bias voltage to the gate of the first upper PMOS device when the I/O pad is in an output mode and V_{DDO} voltage otherwise;
 - a second bias circuit coupled to a gate of the second lower NMOS device, said bias circuit providing a second bias

voltage to the gate of the second lower NMOS device when the I/O pad is in an output mode and a ground voltage otherwise;

a third bias circuit coupled to a gate of the second upper PMOS device, said bias circuit providing a third bias voltage to the gate of the second upper MOS device depending on the voltage on the I/O pad (V_{PAD}) said third bias circuit comprising a capacitive voltage divider; and

a fourth bias circuit coupled to a gate of the first lower NMOS device, said bias circuit providing a fourth bias voltage to the gate of the first lower MOS device.

11. The apparatus of claim 10 wherein the capacitive voltage divider proportions a difference in voltage at the pad and a power supply voltage to derive the third bias voltage when the pad is switching.

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